

**Table 3. ESD Protection Characteristics**

Test Methodology	Class
Human Body Model (per JESD22-A114)	2 (Minimum)
Machine Model (per EIA/JESD22-A115)	A (Minimum)
Charge Device Model (per JESD22-C101)	IV (Minimum)

**Table 4. Electrical Characteristics** ( $T_A = 25^\circ\text{C}$  unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
----------------	--------	-----	-----	-----	------

**Off Characteristics**

Zero Gate Voltage Drain Leakage Current ( $V_{DS} = 65\text{ Vdc}$ , $V_{GS} = 0\text{ Vdc}$ )	$I_{DSS}$	—	—	10	$\mu\text{Adc}$
Zero Gate Voltage Drain Leakage Current ( $V_{DS} = 28\text{ Vdc}$ , $V_{GS} = 0\text{ Vdc}$ )	$I_{DSS}$	—	—	1	$\mu\text{Adc}$
Gate-Source Leakage Current ( $V_{GS} = 5\text{ Vdc}$ , $V_{DS} = 0\text{ Vdc}$ )	$I_{GSS}$	—	—	1	$\mu\text{Adc}$

**On Characteristics**

Gate Threshold Voltage ( $V_{DS} = 10\text{ Vdc}$ , $I_D = 172\ \mu\text{Adc}$ )	$V_{GS(th)}$	1.2	2.0	2.7	Vdc
Gate Quiescent Voltage ( $V_{DD} = 28\text{ Vdc}$ , $I_D = 900\text{ mAdc}$ , Measured in Functional Test)	$V_{GS(Q)}$	1.5	2.6	3.0	Vdc
Drain-Source On-Voltage ( $V_{GS} = 10\text{ Vdc}$ , $I_D = 1.7\text{ Adc}$ )	$V_{DS(on)}$	0.1	0.24	0.3	Vdc

**Functional Tests** <sup>(1)</sup> (In Freescale Test Fixture, 50 ohm system)  $V_{DD} = 28\text{ Vdc}$ ,  $I_{DQ} = 900\text{ mA}$ ,  $P_{out} = 28\text{ W Avg.}$ ,  $f = 2690\text{ MHz}$ , Single-Carrier W-CDMA, IQ Magnitude Clipping, Input Signal PAR = 7.5 dB @ 0.01% Probability on CCDF. ACPR measured in 3.84 MHz Channel Bandwidth @  $\pm 5\text{ MHz}$  Offset.

Power Gain	$G_{ps}$	14.5	15.6	17.5	dB
Drain Efficiency	$\eta_D$	28.0	31.1	—	%
Output Peak-to-Average Ratio @ 0.01% Probability on CCDF	PAR	5.7	6.2	—	dB
Adjacent Channel Power Ratio	ACPR	—	-36.7	-34.5	dBc
Input Return Loss	IRL	—	-14	-9	dB

**Typical Broadband Performance** (In Freescale Test Fixture, 50 ohm system)  $V_{DD} = 28\text{ Vdc}$ ,  $I_{DQ} = 900\text{ mA}$ ,  $P_{out} = 28\text{ W Avg.}$ , Single-Carrier W-CDMA, IQ Magnitude Clipping, Input Signal PAR = 7.5 dB @ 0.01% Probability on CCDF. ACPR measured in 3.84 MHz Channel Bandwidth @  $\pm 5\text{ MHz}$  Offset.

Frequency	$G_{ps}$ (dB)	$\eta_D$ (%)	Output PAR (dB)	ACPR (dBc)	IRL (dB)
2620 MHz	15.5	31.5	6.3	-38.0	-13
2655 MHz	15.5	31.1	6.3	-37.3	-14
2690 MHz	15.6	31.1	6.2	-36.7	-14

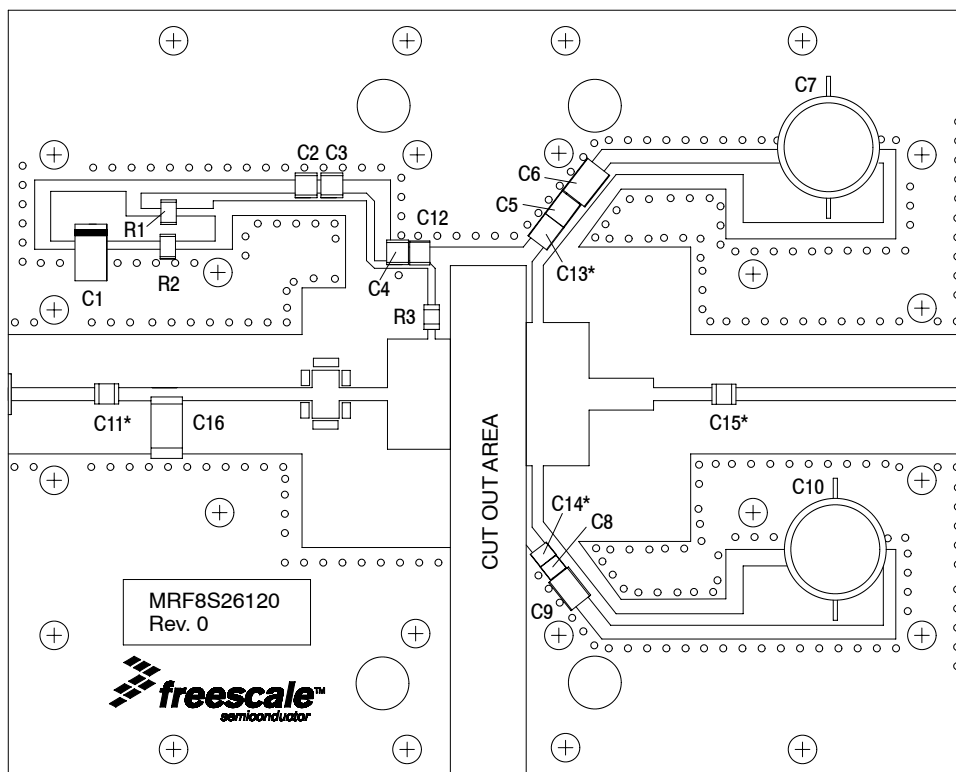
1. Part internally matched both on input and output.

(continued)

**Table 4. Electrical Characteristics** ( $T_A = 25^\circ\text{C}$  unless otherwise noted) (continued)

Characteristic	Symbol	Min	Typ	Max	Unit
<b>Typical Performances</b> (In Freescale Test Fixture, 50 ohm system) $V_{DD} = 28\text{ Vdc}$ , $I_{DQ} = 900\text{ mA}$ , 2620–2690 MHz Bandwidth					
$P_{out}$ @ 1 dB Compression Point, CW	P1dB	—	110	—	W
IMD Symmetry @ 80 W PEP, $P_{out}$ where IMD Third Order Intermodulation $\cong 30\text{ dBc}$ (Delta IMD Third Order Intermodulation between Upper and Lower Sidebands > 2 dB)	IMD <sub>sym</sub>	—	18	—	MHz
VBW Resonance Point (IMD Third Order Intermodulation Inflection Point)	VBW <sub>res</sub>	—	65	—	MHz
Gain Flatness in 70 MHz Bandwidth @ $P_{out} = 28\text{ W Avg.}$	G <sub>F</sub>	—	0.1	—	dB
Gain Variation over Temperature ( $-30^\circ\text{C}$ to $+85^\circ\text{C}$ )	$\Delta G$	—	0.015	—	dB/ $^\circ\text{C}$
Output Power Variation over Temperature ( $-30^\circ\text{C}$ to $+85^\circ\text{C}$ ) (1)	$\Delta P_{1dB}$	—	0.007	—	dB/ $^\circ\text{C}$

1. Exceeds recommended operating conditions. See CW operation data in Maximum Ratings table.



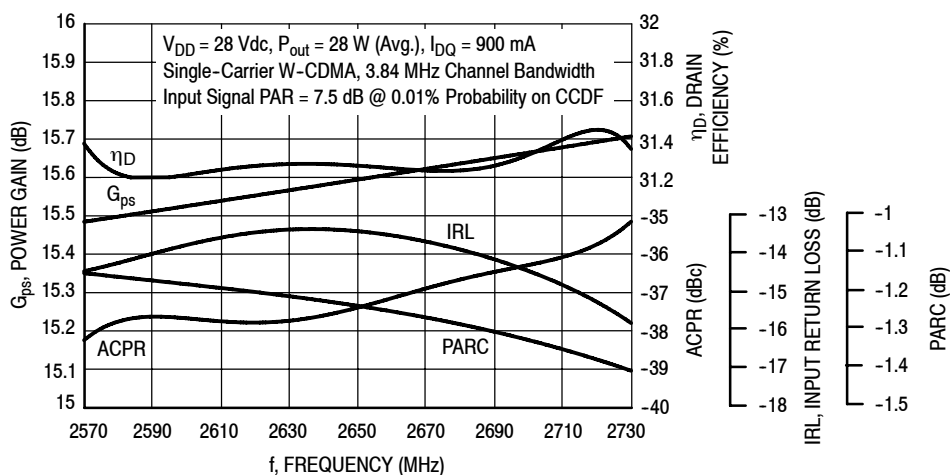
\*C11, C13, C14, and C15 are mounted vertically.

Figure 1. MRF8S26120HR3(HSR3) Test Circuit Component Layout

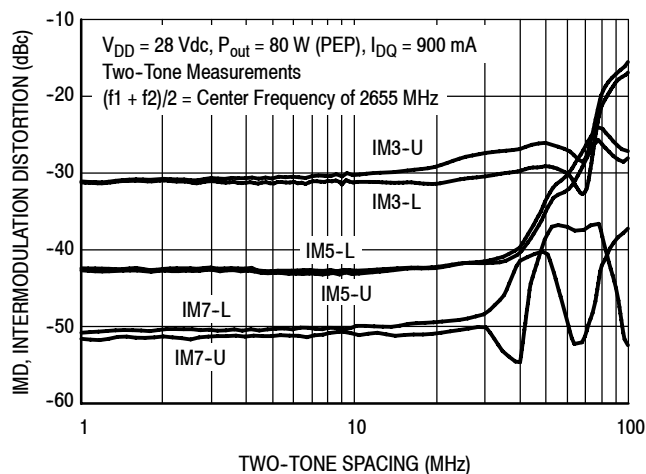
Table 5. MRF8S26120HR3(HSR3) Test Circuit Component Designations and Values

Part	Description	Part Number	Manufacturer
C1	22 $\mu$ F, 35 V Tantalum Capacitor	T494X226K035AT	Kemet
C2	330 nF, 100 V Chip Capacitor	C3225X7R2A334KT	TDK
C3	15 nF, 100 V Chip Capacitor	C3225C0G2A153JT	TDK
C4, C5, C8	2.2 $\mu$ F, 100 V Chip Capacitors	C3225X7R2A225KT	TDK
C6, C9	22 $\mu$ F, 50 V Chip Capacitors	C5750JF1H226ZT	TDK
C7, C10	470 $\mu$ F, 63 V Electrolytic Capacitors	MCGPR63V477M13X26-RH	Multicomp
C11, C12, C13, C14, C15	27 pF Chip Capacitors	ATC800B270JT500XT	ATC
C16	0.8 pF Chip Capacitor	ATC100B0R8BT500XT	ATC
R1	1 k $\Omega$ , 1/4 W Chip Resistor	CRCW12061K00FKEA	Vishay
R2	10 k $\Omega$ , 1/4 W Chip Resistor	CRCW120610K0FKEA	Vishay
R3	7.5 $\Omega$ , 1/4 W Chip Resistor	CRCW12067R50FNEA	Vishay
PCB	0.030", $\epsilon_r = 3.5$	RF-35	Taconic

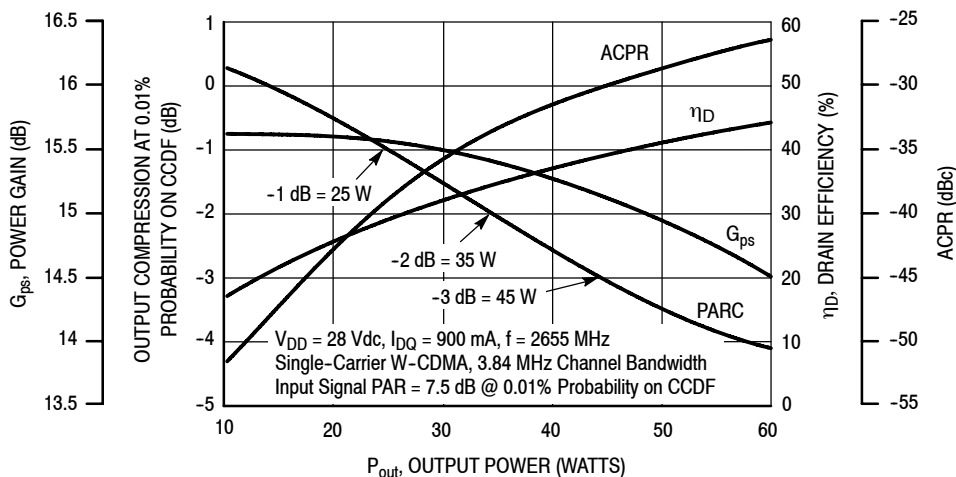
### TYPICAL CHARACTERISTICS



**Figure 2. Output Peak-to-Average Ratio Compression (PARC) Broadband Performance @  $P_{out} = 28$  Watts Avg.**

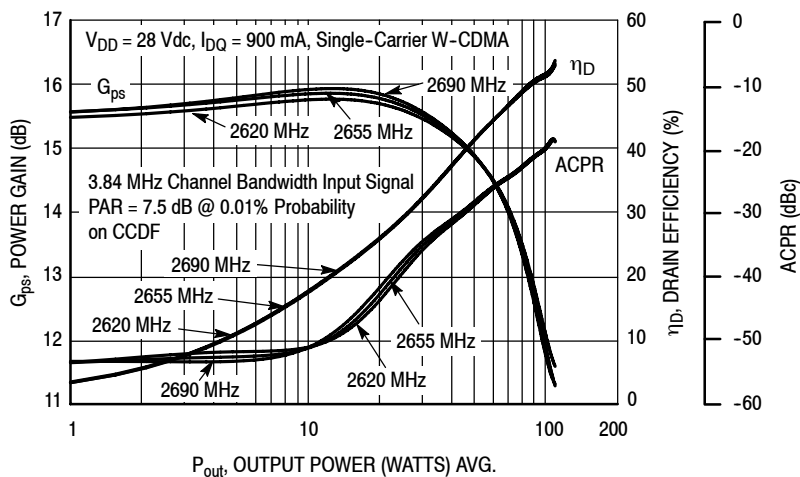


**Figure 3. Intermodulation Distortion Products versus Two-Tone Spacing**

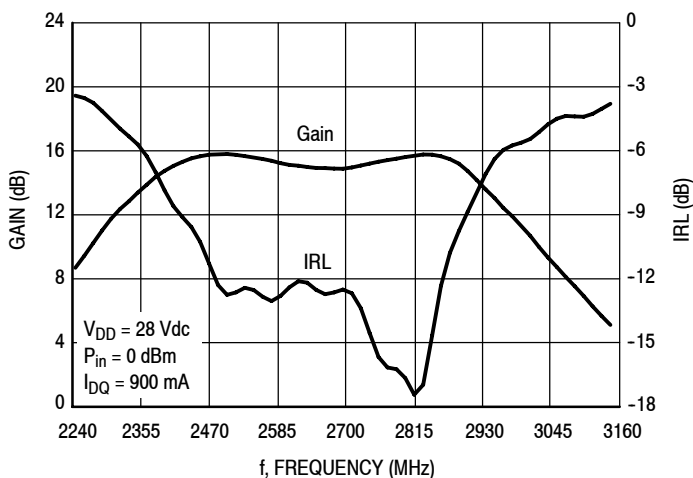


**Figure 4. Output Peak-to-Average Ratio Compression (PARC) versus Output Power**

### TYPICAL CHARACTERISTICS

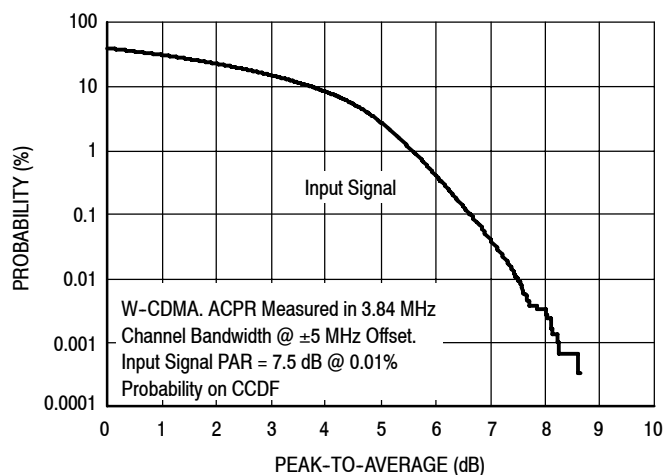


**Figure 5. Single-Carrier W-CDMA Power Gain, Drain Efficiency and ACPR versus Output Power**

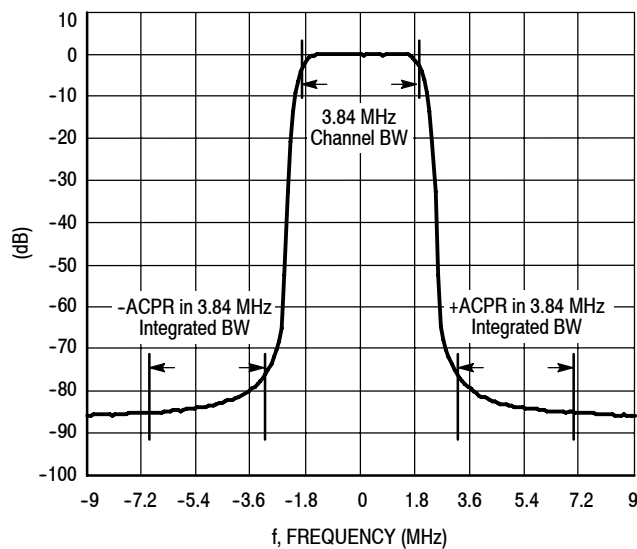


**Figure 6. Broadband Frequency Response**

### W-CDMA TEST SIGNAL



**Figure 7. CCDF W-CDMA IQ Magnitude Clipping, Single-Carrier Test Signal**



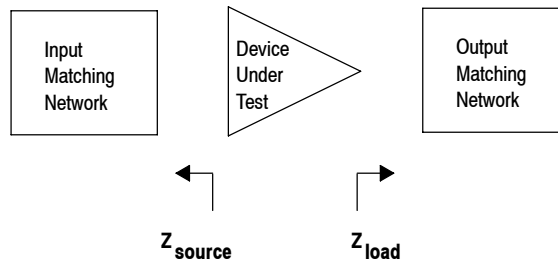
**Figure 8. Single-Carrier W-CDMA Spectrum**

$V_{DD} = 28 \text{ Vdc}$ ,  $I_{DQ} = 900 \text{ mA}$ ,  $P_{out} = 28 \text{ W Avg.}$

f MHz	$Z_{source}$ $\Omega$	$Z_{load}$ $\Omega$
2570	5.21 - j5.62	3.17 - j4.27
2590	5.26 - j5.33	3.15 - j4.20
2610	5.31 - j5.02	3.12 - j4.12
2630	5.35 - j4.71	3.10 - j4.04
2650	5.39 - j4.39	3.07 - j3.96
2670	5.46 - j4.05	3.06 - j3.88
2690	5.53 - j3.77	3.06 - j3.82
2710	5.57 - j3.47	3.05 - j3.77
2730	5.59 - j3.15	3.05 - j3.73

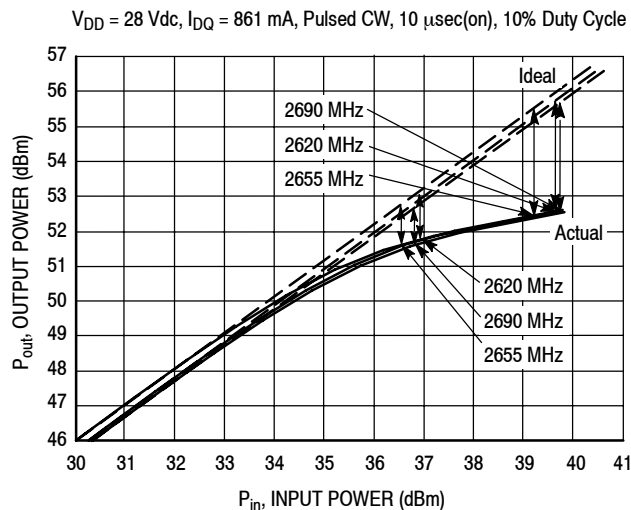
$Z_{source}$  = Test circuit impedance as measured from gate to ground.

$Z_{load}$  = Test circuit impedance as measured from drain to ground.



**Figure 9. Series Equivalent Source and Load Impedance**

## ALTERNATIVE PEAK TUNE LOAD PULL CHARACTERISTICS



NOTE: Load Pull Test Fixture Tuned for Peak P1dB Output Power @ 28 V

f (MHz)	P1dB		P3dB	
	Watts	dBm	Watts	dBm
2620	149	51.7	182	52.6
2655	144	51.6	177	52.5
2690	146	51.6	179	52.5

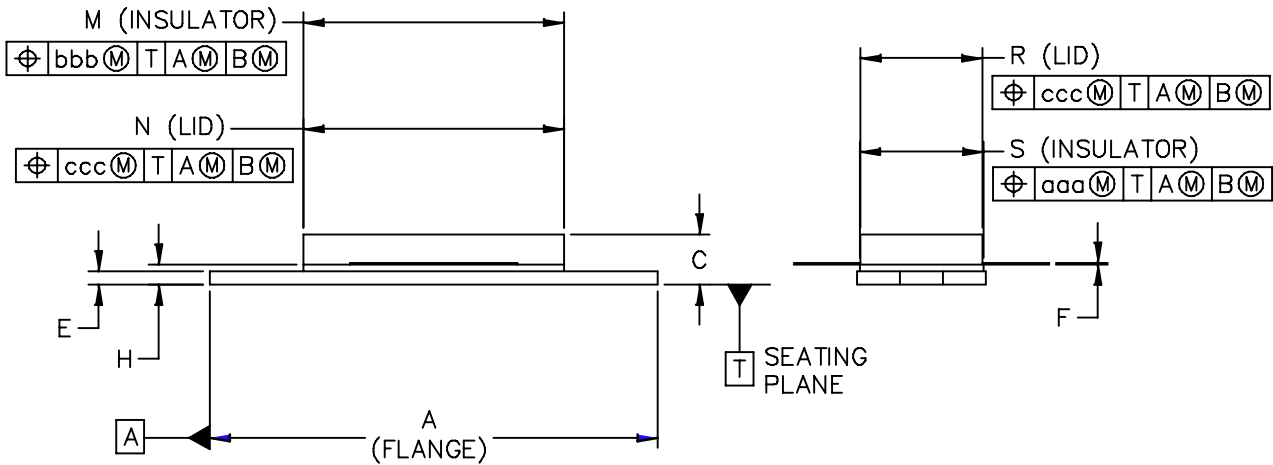
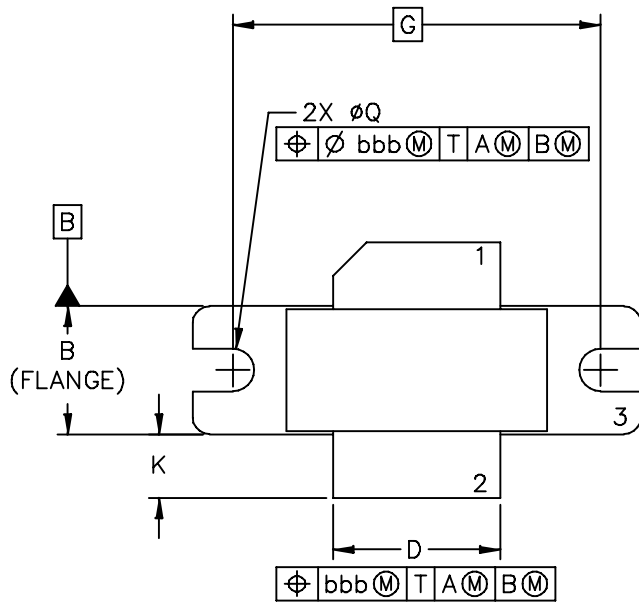
Test Impedances per Compression Level

f (MHz)		$Z_{source}$ $\Omega$	$Z_{load}$ $\Omega$
2620	P1dB	5.83 - j7.00	1.44 - j2.87
2655	P1dB	7.87 - j6.87	1.72 - j3.15
2690	P1dB	9.46 - j5.13	1.52 - j3.20

**Figure 10. Pulsed CW Output Power versus Input Power @ 28 V**



**PACKAGE DIMENSIONS**



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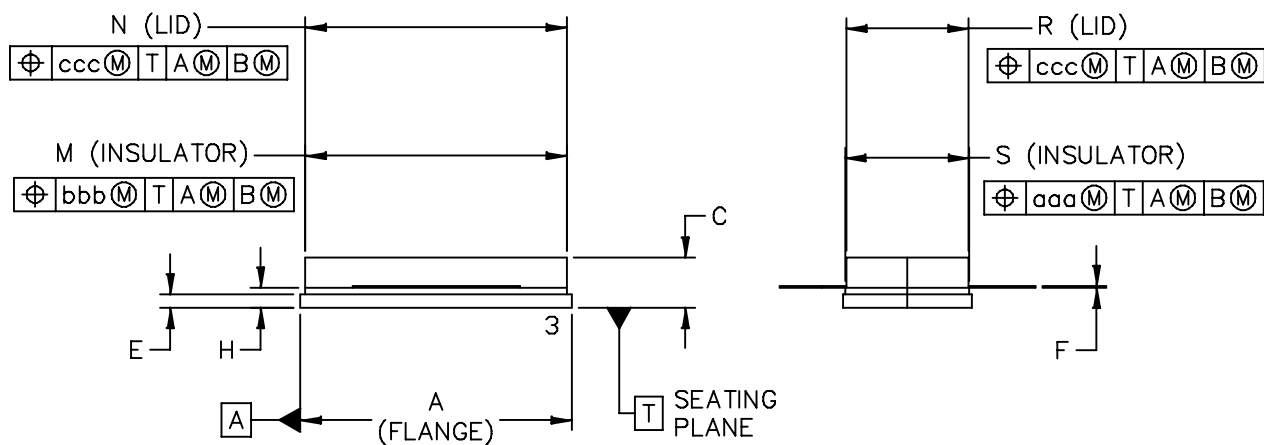
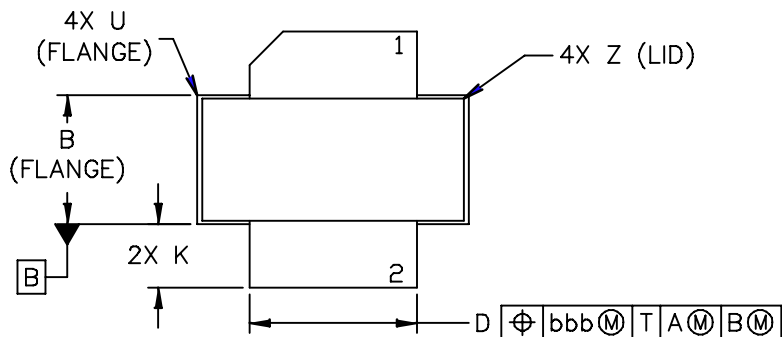
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STYLE 1:

- PIN 1. DRAIN  
 2. GATE  
 3. SOURCE

DIM	INCH		MILLIMETER		DIM	INCH		MILLIMETER	
	MIN	MAX	MIN	MAX		MIN	MAX	MIN	MAX
A	1.335	1.345	33.91	34.16	R	.365	.375	9.27	9.53
B	.380	.390	9.65	9.91	S	.365	.375	9.27	9.52
C	.125	.170	3.18	4.32	aaa	—	.005	—	0.127
D	.495	.505	12.57	12.83	bbb	—	.010	—	0.254
E	.035	.045	0.89	1.14	ccc	—	.015	—	0.381
F	.003	.006	0.08	0.15	—	—	—	—	—
G	1.100 BSC		27.94 BSC		—	—	—	—	—
H	.057	.067	1.45	1.7	—	—	—	—	—
K	.170	.210	4.32	5.33	—	—	—	—	—
M	.774	.786	19.66	19.96	—	—	—	—	—
N	.772	.788	19.6	20	—	—	—	—	—
Q	Ø.118	Ø.138	Ø3	Ø3.51	—	—	—	—	—

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STYLE 1:

- PIN 1. DRAIN
2. GATE
3. SOURCE

DIM	INCH		MILLIMETER		DIM	INCH		MILLIMETER	
	MIN	MAX	MIN	MAX		MIN	MAX	MIN	MAX
A	.805	-.815	20.45	20.7	U	-.040	-	-	1.02
B	.380	-.390	9.65	9.91	Z	-.030	-	-	0.76
C	.125	-.170	3.18	4.32	aaa	-.005	-	-	0.127
D	.495	-.505	12.57	12.83	bbb	-.010	-	-	0.254
E	.035	-.045	0.89	1.14	ccc	-.015	-	-	0.381
F	.003	-.006	0.08	0.15	-	-	-	-	-
H	.057	-.067	1.45	1.7	-	-	-	-	-
K	.170	-.210	4.32	5.33	-	-	-	-	-
M	.774	-.786	19.61	20.02	-	-	-	-	-
N	.772	-.788	19.61	20.02	-	-	-	-	-
R	.365	-.375	9.27	9.53	-	-	-	-	-
S	.365	-.375	9.27	9.52	-	-	-	-	-

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## PRODUCT DOCUMENTATION AND SOFTWARE

Refer to the following documents, tools and software to aid your design process.

### Application Notes

- AN1955: Thermal Measurement Methodology of RF Power Amplifiers

### Engineering Bulletins

- EB212: Using Data Sheet Impedances for RF LDMOS Devices

### Software

- Electromigration MTTF Calculator
- RF High Power Model
- .s2p File

For Software, do a Part Number search at <http://www.freescale.com>, and select the “Part Number” link. Go to the Software & Tools tab on the part’s Product Summary page to download the respective tool.

## REVISION HISTORY

The following table summarizes revisions to this document.

Revision	Date	Description
0	June 2010	• Initial Release of Data Sheet

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